

ECE 445: Biomedical Instrumentation

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Sensor Systems

Typically interested in electronic sensor

- convert desired parameter into electrically measurable signal
- General Electronic Sensor
 - <u>primary transducer</u>: changes "real world" parameter into electrical signal
 - <u>secondary transducer</u>: converts electrical signal into analog or digital values





Primary Transducers

Conventional Transducers

large, but generally reliable, based on older technology

- thermocouple: temperature difference
- compass (magnetic): direction
- Microelectronic Sensors
 millimeter sized, highly sensitive, less robust
 - photodiode/phototransistor: photon energy (light)
 - infrared detectors, proximity/intrusion alarms
 - piezoresisitve pressure sensor: air/fluid pressure
 - microaccelerometers: vibration, Δ-velocity (car crash)
 - chemical senors: O₂, CO₂, Cl, Nitrates (explosives)
 - DNA arrays: match DNA sequences

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Direct vs. Indirect Measurement

- Direct Measurement:
 - When sensor *directly* measures parameter of interest
 - Example, displacement sensor measuring diameter of blood vessel
 - Example, ??

• Indirect Measurement:

- When sensor measures a parameter that can be translated into the parameter of interest
- Example, displacement sensor measuring movement of a microphone diaphragm to quantify liquid movement through the heart
- Example, ??

Displacement Measurements







Strain Gage: Materials

material	gage factor, G	TCR (10 ⁻⁵)	
Ni ₈₀ Cr ₂₀	2.1 - 2.6	10	
Pt ₉₂ W ₈	3.6 - 4.4	24	
Silicon (n type)	-100 to -140	70 to 700	
Germanium (p type)	102		

TCR = temperature coefficient of resistivity (°C⁻¹)

- Note:
 - G for semiconductor materials ~ 50-70 x that of metals
 due to stronger piezoresistive effect
 - semiconductors have much higher TCR
 - requires temperature compensation in strain gage





Wheatstone Bridge





- Ri voltmeter internal resistance
- Temperature Compensation
 - When all R's from same material
 - TCR of all elements cancel
 - change in temperature \rightarrow no change in output voltage



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Semiconductor Strain Gage

- Semiconductors
 - make highly sensitive strain gages
 - have higher gage factors than metals/alloys
 - more temperature sensitive than metals/alloys
 - less linear than metals/alloys

Semiconductor strain gage options

- bulk semiconductor material
 - p-type: positive gage factor
 - n-type: negative gage factor
 - lightly doped material gives high gage factor
- diffused/doped semiconductor



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Semiconductor Strain Gage

- Cantilever-beam force sensor
 - 2 piezoresistors in top and two in bottom of a semiconductor beam
 - when force F is applied
 - R1 & R3 (on top) are compressed
 - R2 & R4 (on bottom) are stretched









Step response for displace x at time T

combined C's and R's

- exponential decay due to leakage through internal resistance note: piezoelectric devices have ~1G-ohm internal resistances
- decay and undershoot can be reduced by increasing RC time constant





Temperature Sensor Options

Thermoelectric Devices • most common type is called *Thermocouple* can be made small enough to place inside catheters or hypodermic needles Resistance Temperature Detectors (RTDs) metal resistance changes with temperature $R_{\tau} = R_{\alpha} [1 + \alpha_{\tau} T + \alpha_{\sigma} T^{2} + \cdots + \alpha_{\sigma} T^{n} +] \cong R_{\alpha} [1 + \alpha_{\tau} T]$ Platinum, Nickel, Copper metals are typically used positive temperature coefficients Thermistors ("thermally sensitive resistor") formed from semiconductor materials, not metals $R_{T} = R_{0} \exp \left[B\left(\frac{1}{T} - \frac{1}{T_{0}}\right)\right]$ • often composite of a ceramic and a metallic oxide (Mn, Co, Cu or Fe) typically have negative temperature coefficients Radiant Temperature Sensors photon energy changes with temperature measured optically (by photo detector) Integrated Circuit (IC) Temperature Sensors various temperature effects in silicon manipulated by circuits • proportional to absolute temperature (PTAT) circuit: Si bandgap = f(Temp)ECE 445: Biomedical Instrumentation Sensors p. 27

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Temperature Sensor Options

• Comparison of common temperature sensors

	THERMOCOUPLES	RTD	IC
ACCURACY	Limits of error wider than RTD or IC Sensor	Better accuracy than thermocouple	Best accuracy
RUGGEDNESS	Excellent	Sensitive to strain and shock	Sensitive to shock
TEMPERATURE	-400 to 4200° F	-200 to 1475° F	-70 to 300° F
DRIFT	Higher than RTD	Lower than TC	
LINEARITY	Very non-linear	Slightly non-linear	Very linear
RESPONSE	Fast dependent on size	Slow due to thermal mass	Faster than RTD
COST	Rather inexpensive except for noble metals TCs, which are very expensive	More expensive	Low cost





Electromagnetic Radiation Spectrum









- measures magnitude of infrared radiation from tympanic membrane & surrounding ear canal
 - tympanic membrane is perfused by the same vasculature as the hypothalamus, the body's main thermostat
- advantages over thermometers, thermocouples or thermistors
 - does not need to make contact to set temperature of the sensor
 - fast response time, ~0.1sec
 - accuracy ~ 0.1°C
 - independent of user technique or patient activity
- requires calibration target to maintain accuracy

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	Fiber-optic Temperature Ser	MICHIGAN STAT UNIVERSIT
 Sensor small pends of light e percertempe Can be 	Operation prism-shaped sample of single-crystal undoped G of two optical fibers nergy absorbed by the GaAs crystal depends on the ntage of received vs. transmitted energy is a func- prature made small enough for biological implan	aAs attached to temperature tion of tation
=	Epoxy Transmit fiber 0.23 Receive fiber	5 mm
-		







5000

1000

V B G YOR

2000

Radiation Sensors

detector

Relative

2 0 200

1.0 Thermal

- Spectral response
 - Si, no response above 1100nm
 - special materials (InSb)
 - monitor skin radiation (300K)
- Thermal sensors
 - transforms radiation into heat
 - flat spectral response but slow
 - subject to error from changes in ambient temperature
 - example thermal sensors: thermistors, thermocouples
- Quantum sensors
 - transform photon energy into electron release
 - · sensitive over a limited spectrum of wavelengths
 - example quantum sensors: eye, photographic emulsion, sensors below
 - Photoemissive sensors, e.g. phototube
 - Photoconductive cells
 - Photojunction sensors
 - Photovoltaic sensors

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Light

Level

photoresistor

photodiode

0 mW/cm²

10

Dark

Iλ

 $I=I_0[exp(eV/kT)-1]-I_\lambda$ I_{λ} is proportion to the light level

100mV, 500mV, 600

Current

Solid-State Photoelectric Sensors

Photoconductive cells

- photoresistor
 - photosensitive crystalline material such as CdS or PbS
 - incoming radiation causes electrons to jump band gap and produce electron-hole pairs \rightarrow lower resistance
- Photojunction sensors
 - incoming radiation generates electron-hole pairs in diode depletion region
 - minimum detectable energy based on band gap of the diode substrate (e.g., Si)
 - can be used in photovoltaic mode
 - change in open-circuit voltage is monitored
- Photon coupler



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